

### DESCRIPTION

The HY63V8100A is a high-speed 131,072 x 8-bits CMOS static RAM fabricated using Hyundai's high performance twin tub CMOS process technology. This high reliability process coupled with high-speed circuit design techniques, yields maximum access time of 20ns. The HY63V8100A has a data retention mode that guarantees data to remain valid at a minimum power supply voltage of 2.0 volt. It is suitable for use in high-density high-speed system applications.

### FEATURES

- High speed - 20/25/30/35ns (max.)
- Low power consumption
  - Operating : 100 mA (max.)
  - Standby (TTL) : 20 mA (max.)
  - (CMOS) : 1 mA (max.)
  - : 50  $\mu$ A (max.) - L-part
- Single 3.3V $\pm$  10% power supply
- Battery backup (L-part)
  - 2.0V (min.) data retention
- Fully static operation
  - No clock or refresh required
- TTL compatible inputs and outputs
- Tri-state output
- Standard pin configuration (Revolutionary)
  - 32 pin 400 mil SOJ
  - 32 pin 400 mil TSOP-II

### PIN CONNECTION



### PIN DESCRIPTION

Pin Name	Pin Function
CS	Chip Select
WE	Write Enable
DE	Output Enable
A0-A16	Address Inputs
I/O1-I/O8	Data Input/Output
Vcc	Power (+ 3.3V)
Vss	Ground